

CH3D10065G

Silicon Carbide Schottky Diode

V_{RRM}	=	650	V
$I_F (T_C \leq 135^\circ C)$	=	14.5	A
Q_C	=	25	nC

Features

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V_F
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Package



TO-263-2



Part Number	Package	Marking
CH3D10065G	TO-263-2	CH3D10065G

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V	$T_C = 25^\circ C$	
V_{RSM}	Surge Peak Reverse Voltage	650	V	$T_C = 25^\circ C$	
V_R	DC Blocking Voltage	650	V	$T_C = 25^\circ C$	
I_F	Forward Current	29 14.5 10	A	$T_C \leq 25^\circ C$ $T_C \leq 135^\circ C$ $T_C \leq 153^\circ C$	
I_{FSM}	Non-Repetitive Forward Surge Current	85	A	$T_C = 25^\circ C, t_p = 8.3ms, \text{Half Sine Wave}$	
P_{tot}	Power Dissipation	129	W	$T_C = 25^\circ C$	Fig.3
T_C	Maximum Case Temperature	153	$^\circ C$		
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to 175	$^\circ C$		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.4 1.75	1.65 2.3	V	$I_F = 10A, T_J = 25^\circ C$ $I_F = 10A, T_J = 175^\circ C$	Fig.1
I_R	Reverse Current	1 5	20 100	μA	$V_R = 650V, T_J = 25^\circ C$ $V_R = 650V, T_J = 175^\circ C$	Fig.2
C	Total Capacitance	575 57 46	/	pF	$V_R = 0V, T_J = 25^\circ C, f = 1MHz$ $V_R = 200V, T_J = 25^\circ C, f = 1MHz$ $V_R = 400V, T_J = 25^\circ C, f = 1MHz$	Fig.5
Q_C	Total Capacitive Charge	25	/	nC	$V_R = 650V, I_F = 10A$ $di/dt = 200A/\mu s, T_J = 25^\circ C$	Fig.4

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.16	$^\circ C/W$	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80	$^\circ C/W$	
T_{sold}	Soldering Temperature	260	$^\circ C$	

Typical Performance

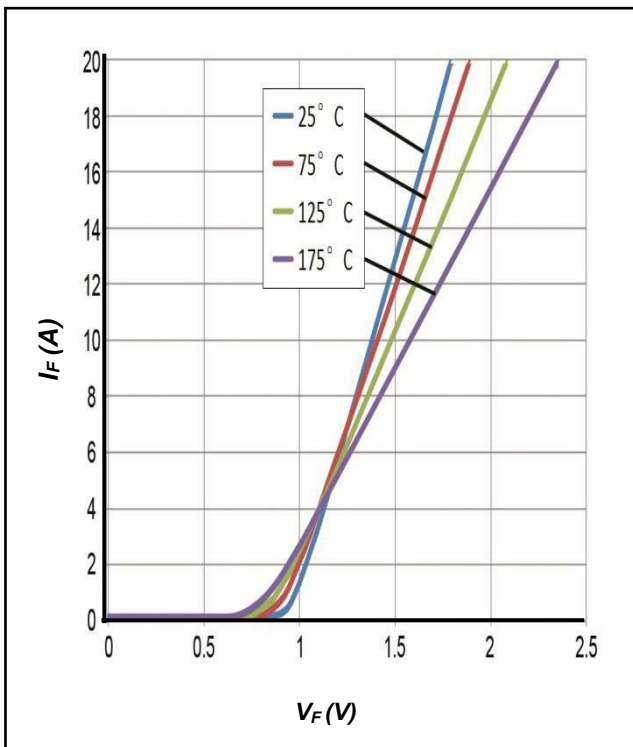


Figure 1. Forward Characteristics

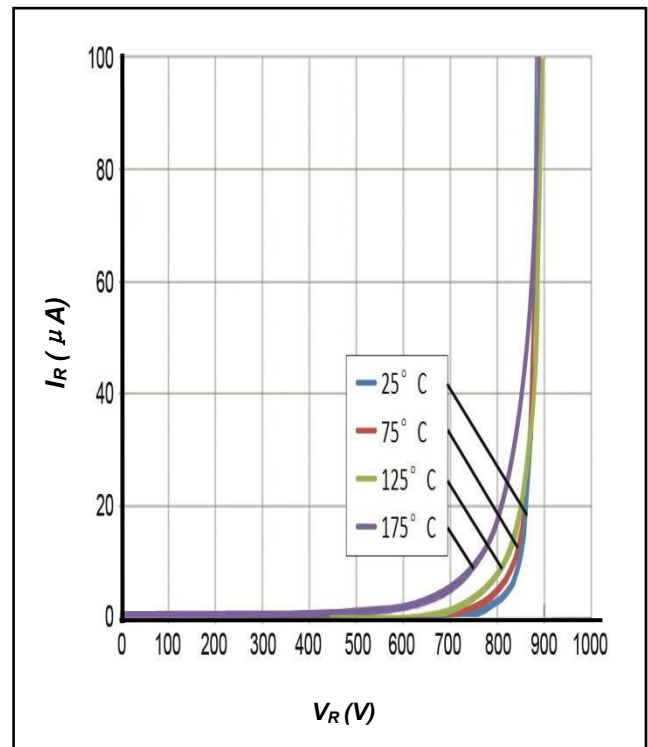


Figure 2. Reverse Characteristics

Typical Performance

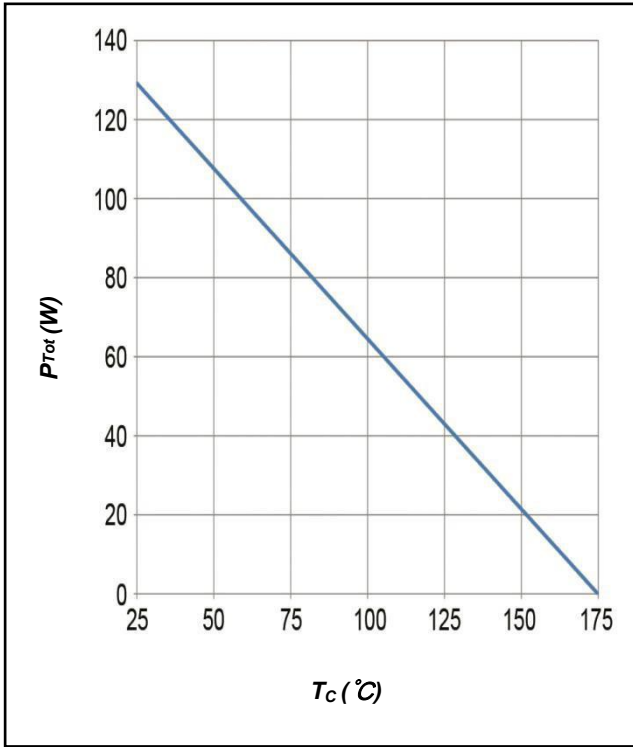


Figure 3. Power Derating

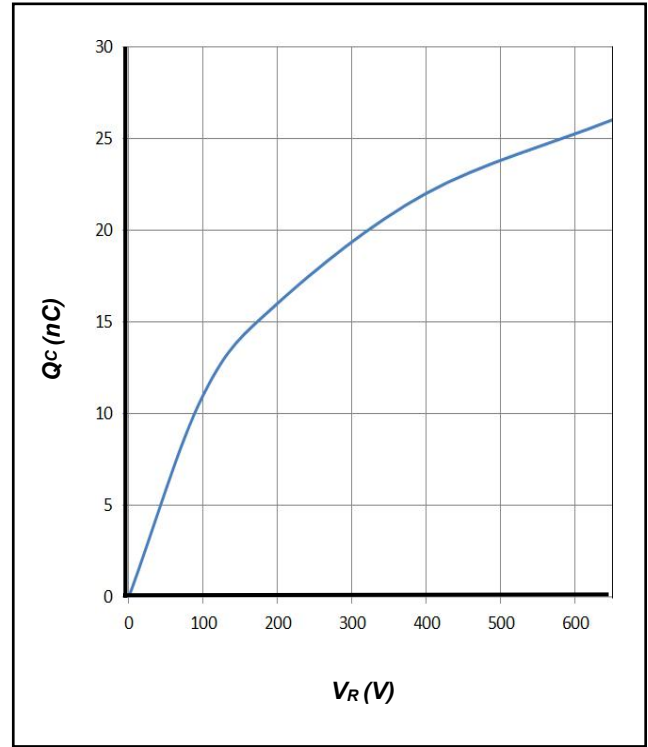


Figure 4. Total Capacitive Charge vs. Reverse Voltage

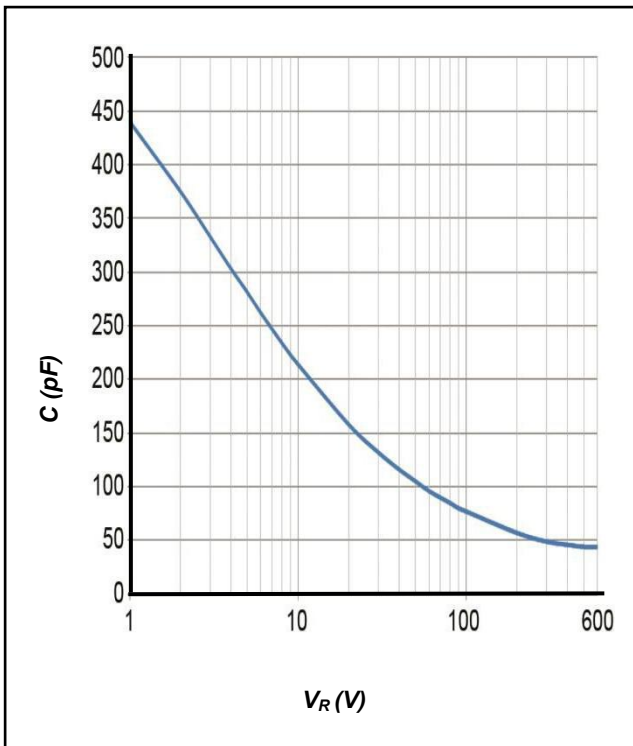


Figure 5. Total Capacitance vs. Reverse Voltage

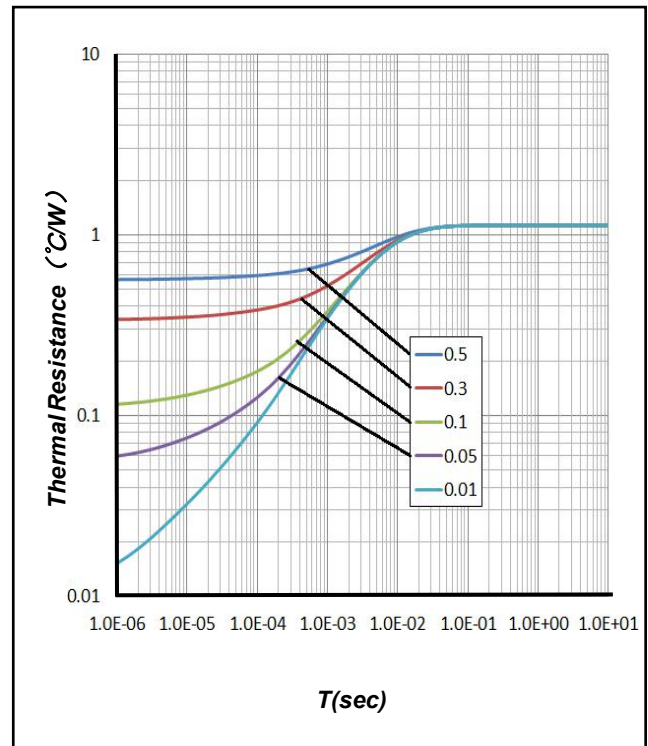
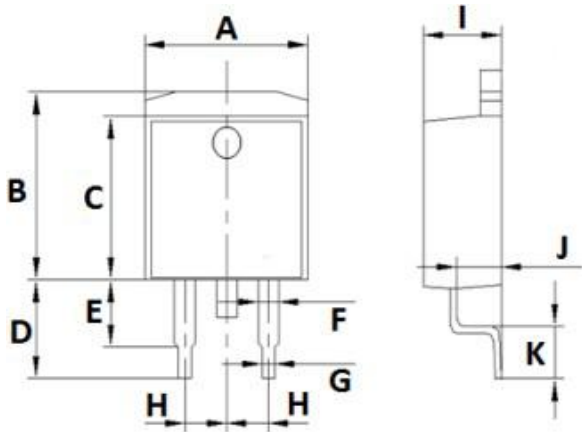


Figure 6. Transient Thermal Impedance

Package Dimensions

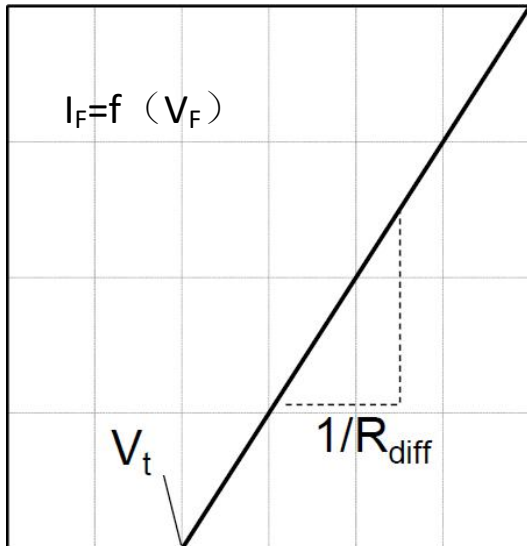
Package TO-263-2



Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
A	9.9	10.1	10.3
B	9.90	10.1	10.3
C	8.50	8.7	8.90
D	4.85	5.05	5.25
E	3.00	3.2	3.40
F	1.05	1.25	1.45
G	0.60	0.8	1.00
H	2.34	2.54	2.74
I	4.40	4.6	4.80
J	2.40	2.6	2.80
K	2.55	1.75	2.95

Simplified Diode Model

Equivalent IV Curve for Model



Mathematical Equation

$$V_F = V_t + I_F \times R_{diff}$$

$$V_t = -0.0011 \times T_j + 0.97 \text{ [V]}$$

$$R_{diff} = 1 \times 10^{-6} \times T_j^2 + 9 \times 10^{-5} \times T_j + 0.043 \text{ [\Omega]}$$

Note:

T_j = Diode Junction Temperature In Degrees Celsius,

valid from 25°C to 175°C

I_F = Forward Current

Less than 20A